DONGGUAN NANJING ELECTRONICS LTD.,

TO-247-4 Silicon Carbide Power MOSFET

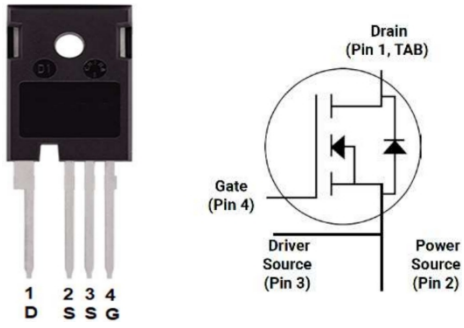
NJ040P120Q SiC MOSFET 1200V, 62A, 35mΩ

General Description

This product family offers state of the art performance. It is designed for high frequency applications here high efficiency and high reliability are required.

Features

- High Blocking Voltage
- High Frequency Operation
- Low on-resistance
- Fast intrinsic diode with low reverse recovery



TO-247-4
Pin definition

Applications

- Motor Drives
- Solar / Wind Inverters
- EV Charging Station
- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies

Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- High Temperature Application
- Hard Switching & Higher Reliability
- Easy to drive

Key performance parameters

Type	V_{DS}	I_D T_C=25℃	$R_{DS(ON)}$
NJ040P120Q	1200V	62A	35mΩ

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Maximum Ratings

T_C=25℃, unless otherwise specified

Parameter	Symbol	Test conditions	Value	Unit
Drain - Source Voltage	V_{DSmax}	V_{GS}= 0V, I_D =100μA	1200	V
Gate - Source Voltage (dynamic)	V_{GSmax}	AC (f>1 Hz)	-10/+25	V
Gate - Source Voltage (static)	V_{GSop}	static	-5/+20	V

Maximum Ratings

T_C=25℃, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous Drain Current: V_{GS} = 20V T_C = 25°C T_C = 100°C	I_D	62 44	A
Pulsed Drain Current: T_C = 25°C	$I_{D(pulse)}$	130	A
Short Circuit Capability : V_{DD} = 800V V_{GS} = 20V	tsc	3	μS
Short Circuit Capability : V_{DD} = 800V V_{GS} = 20V	I_{DS}	600	A
Total power dissipation : T_C = 25°C	P_D	300	W
Operating Junction Temperature :	T_j	-55 to 175	°C
Storage Temperature :	Tstg	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Condition	Typ	Max	Unit
Thermal Resistance (per device)	$R_{th(j-c)}$	junction-case	0.35	0.5	°C/W

Typical Characteristics

T_C =25℃, unless otherwise specified

Parameter	Symbol	Value			Unit	Test Condition
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200			V	V_{GS} = 0V I_D = 100μA
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.8 1.9 1.8	3.9	V	V_{DS} = V_{GS} I_D = 10mA T_J = 150°C T_J = 175°C
Zero Gate Voltage Drain Current	I_{DSS}	0	5	100	μA	V_{DS} = 1200V V_{GS} = 0V
Gate-Source Leakage Current	I_{GSS}	0 -200	10 -10	200 0	nA	V_{GS} = 20V V_{DS} = 0V V_{GS} = -5V V_{DS} = 0V
Drain-Source On-State Resistance	$R_{DS(on)}$		35 54 63	50	mΩ	V_{GS} = 20V I_D = 40 A T_J = 150°C T_J = 175°C
Trans-conductance	gfs		24 22 22		S	V_{GS} = 20V I_D = 40 A T_J = 150°C T_J = 175°C
Input capacitance	C_{iss}		2980		pF	V_{DS} = 1000V V_{GS} = 0V f = 1MHz
Output capacitance	C_{iss}		143			
Reverse transfer capacitance	C_{rss}		15			
Coss Stored Energy	E_{oss}		92		μJ	
Total gate charge	Qg		148		nC	V_{DS} = 800V V_{GS} = -5V / 20V I_D = 40 A
Gate-source charge	Qgs		40			
Gate-drain charge	Qgd		70			
Internal gate input resistance	$R_{g(int)}$		2		Ω	f = 1MHz I_D = 0A
Turn-On Switching Energy	E_{ON}		545		μJ	V_{DS} = 800V V_{GS} = -5V/20V I_D = 40A $R_{G(ext)}$ =1 Ω L= 450μH
Turn-Off Switching Energy	E_{OFF}		355			
Turn-On Delay Time	$t_{d(on)}$		18		ns	V_{DS} = 800V V_{GS} = -5V/20V
Rise Time	tr		34			

Turn-Off Delay Time	$t_{d(off)}$		36			I_D = 40A $R_{G(ext)}$ =1 Ω L = 450μH
Fall Time	t_f		15			
Avalanche Capability	E_{AS}		400		mJ	V_{DD} = 100V V_{GS} =20V L=2mH
	I_A		20		A	

Reverse Diode Characteristics

*T*C =25℃, unless otherwise specified

Parameter	Symbol	Value			Unit	Test Condition
		Min.	Typ.	Max.		
Diode Forward Voltage	V_{SD}		3.9 3.7 3.6		V	V_{GS} = -5V I_{SD} = 20A T_J = 150°C T_J = 175°C
Continuous Diode Forward Current	I_S		60		A	V_{GS} = -5V
Reverse Recovery time	t_{rr}		17		ns	V_{GS} = -5V I_{SD} = 40A V_R = 800V dif/dt = 4200 A/μs
Reverse Recovery Charge	Q_{rr}		310		nC	
Peak Reverse Recovery Current	I_{rrm}		30		A	

Typical Performanc

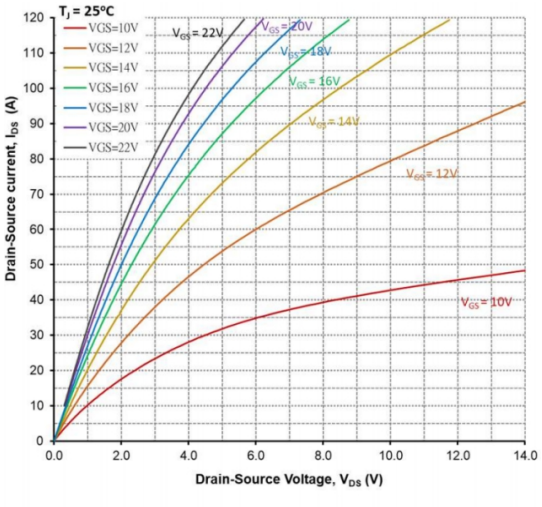


Figure 1. Output Characteristics, T_J = 25°C

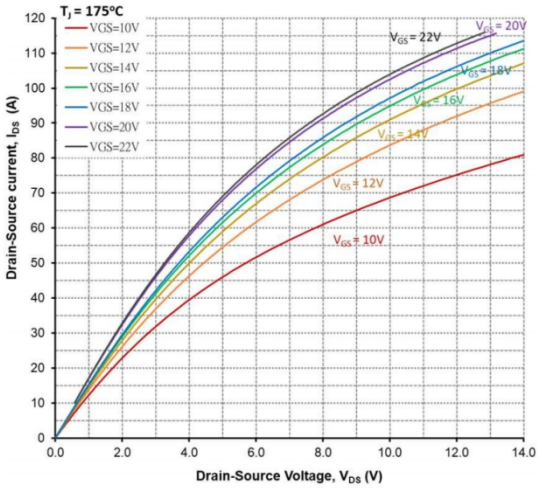


Figure 2. Output Characteristics, T_J = 175°C

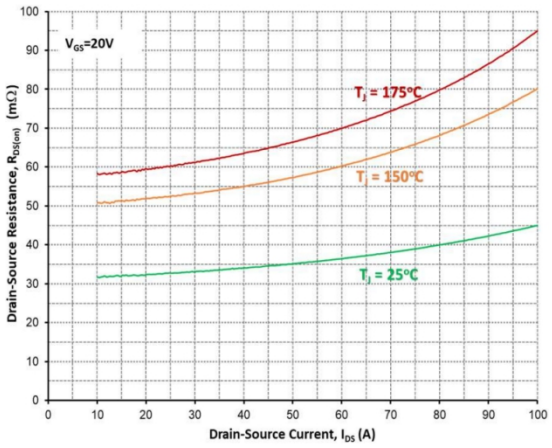


Figure 3. On-Resistance vs. Drain Current For Various Temperatures

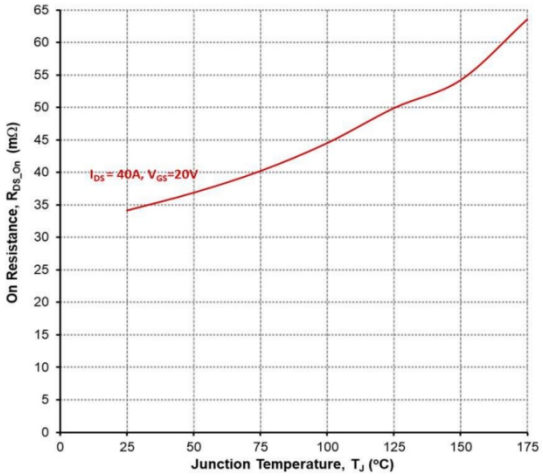


Figure 4. On-Resistance vs. Temperature

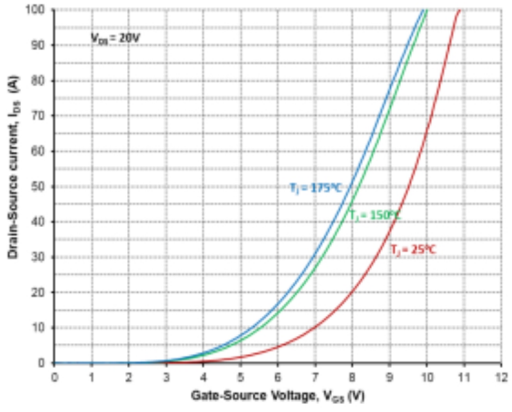


Figure 5. Transfer Characteristic For Various Junction Temperatures

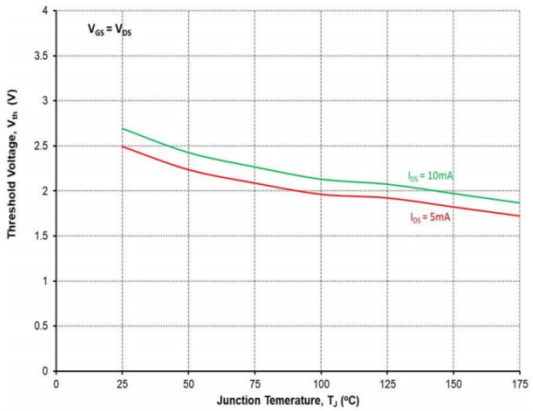


Figure 6. Threshold Voltage vs. Temperature

Typical Characteristics

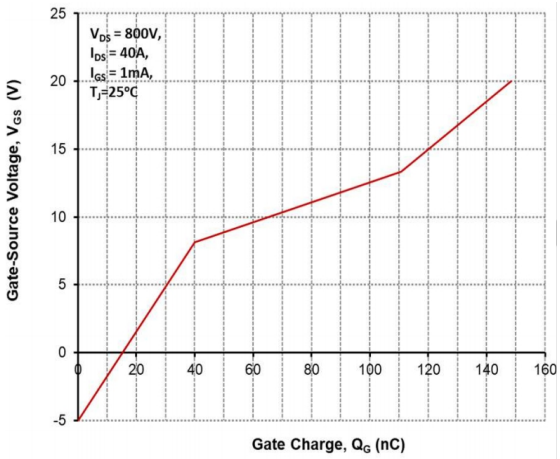


Figure 7. Gate Charge Characteristics

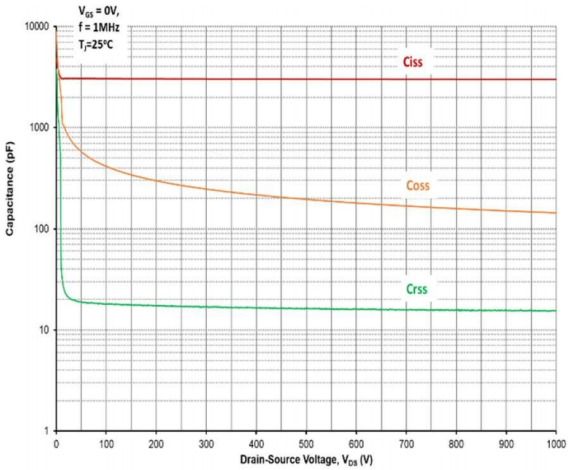


Figure 8. Capacitances vs. Drain-Source Voltage (0-1000V)

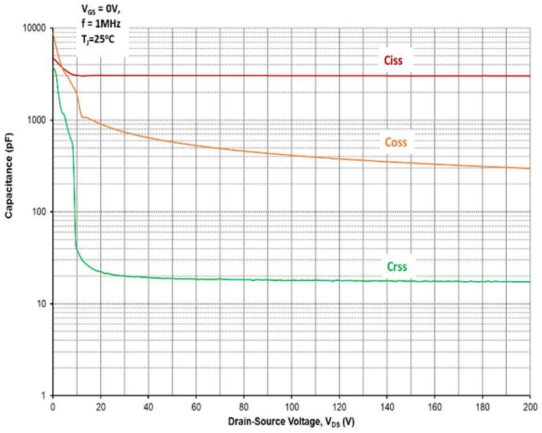


Figure 9. Capacitances vs. Drain-Source Voltage (0-200V)

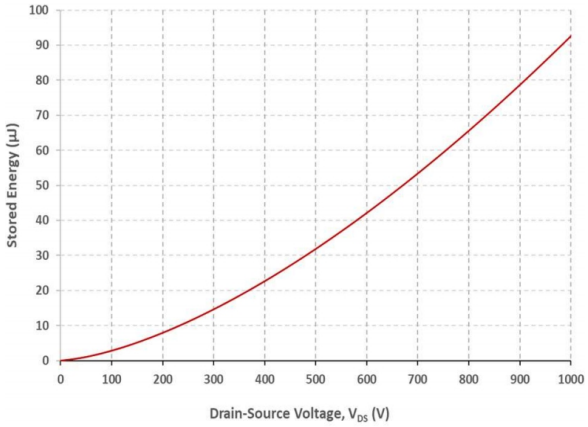


Figure 10. Output Capacitor Stored Energy

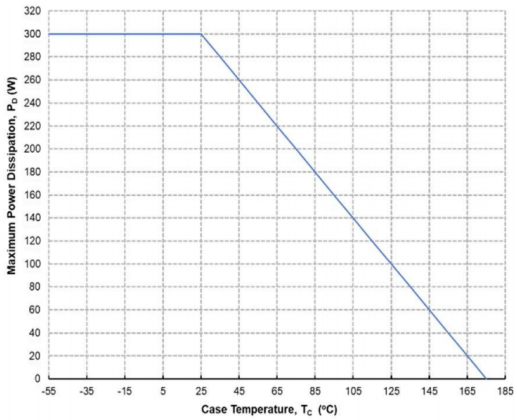


Figure 11. Maximum Power Dissipation Derating vs. Case Temperature

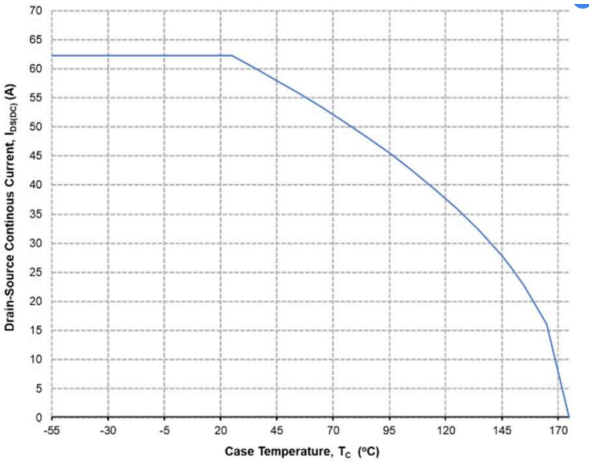


Figure 12. Continuous Drain Current Derating vs. Case Temperature

Typical Characteristics

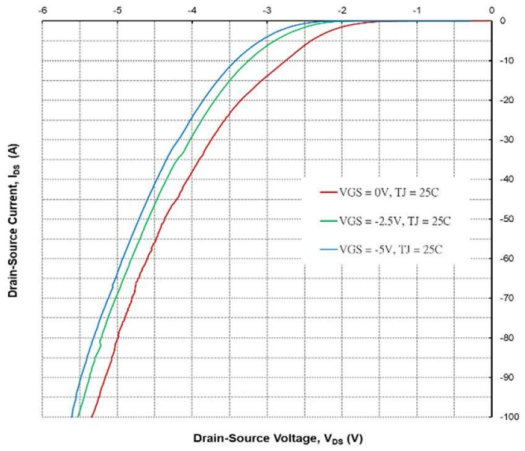


Figure 13. Body Diode Characteristics @ 25°C

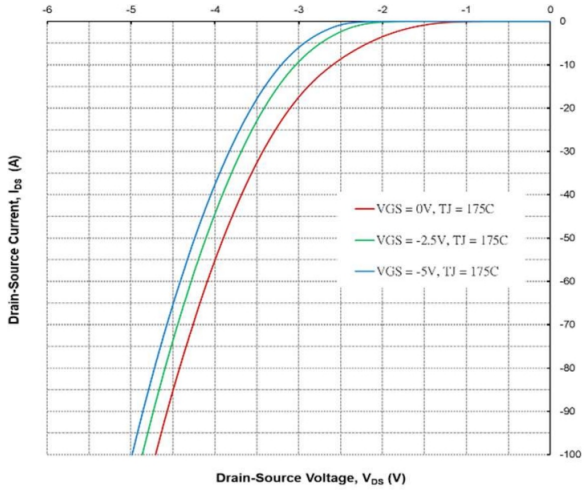


Figure 14. Body Diode Characteristics @ 175°C

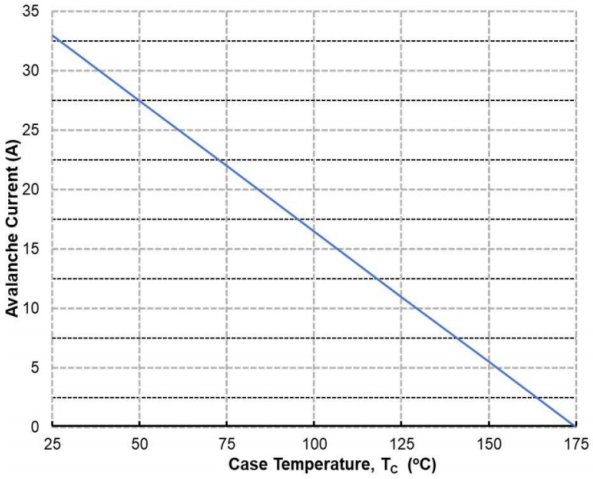


Figure 15. Single Avalanche vs. Temperature

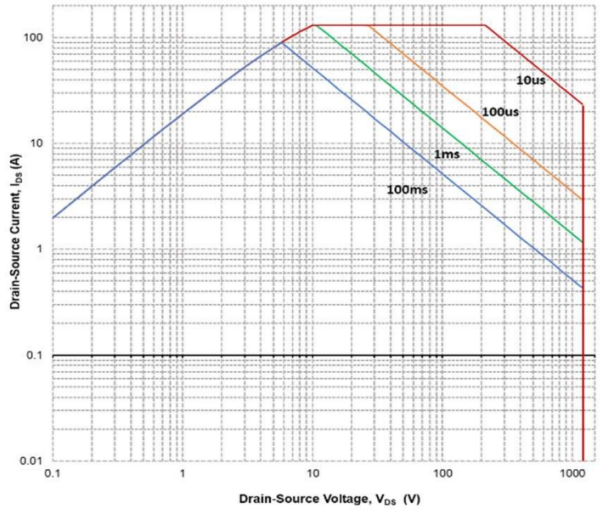
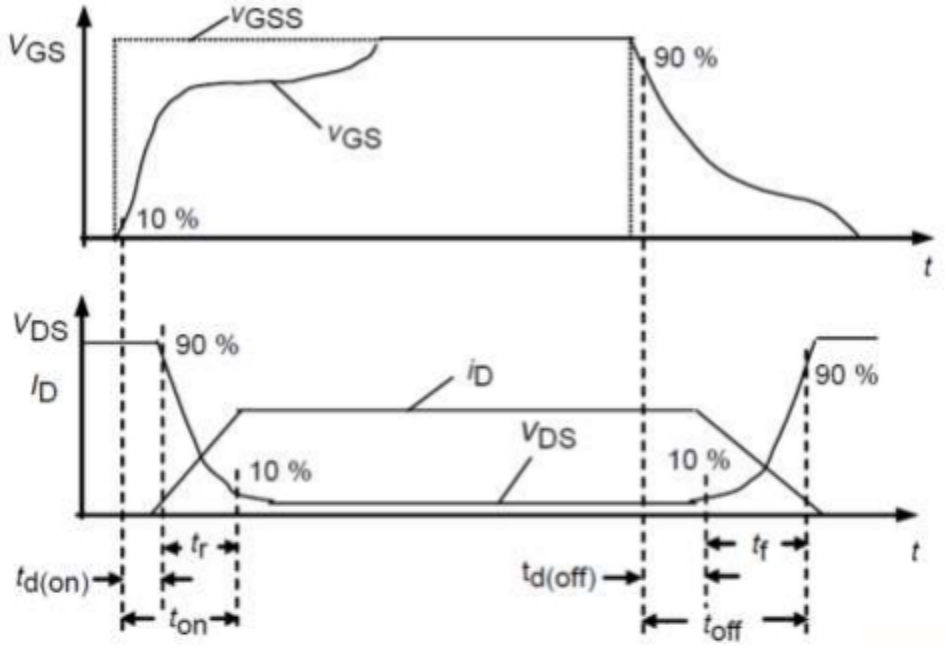
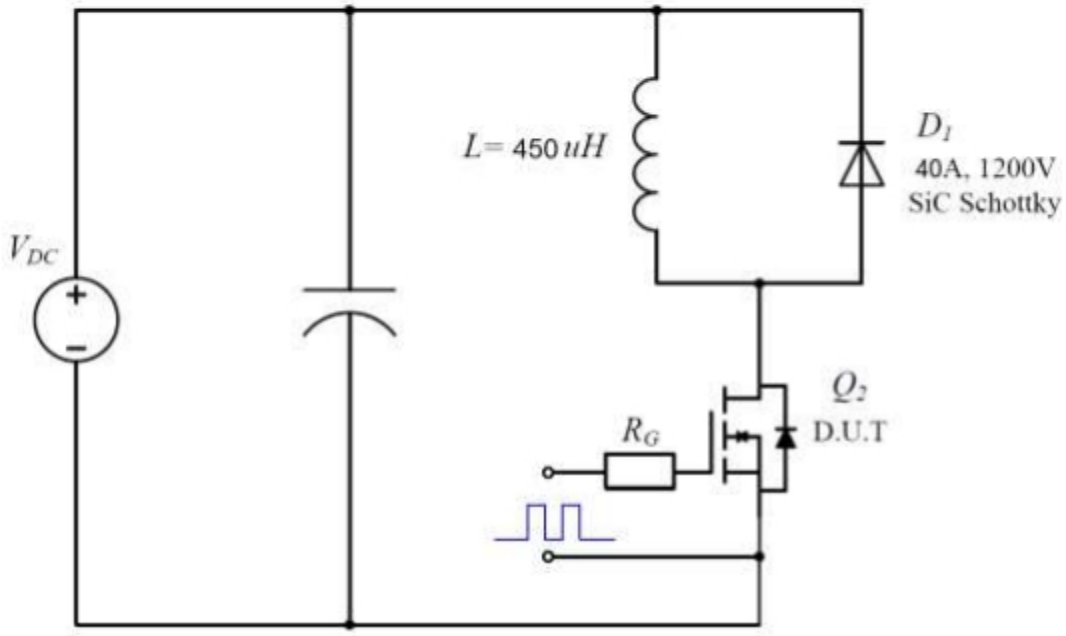


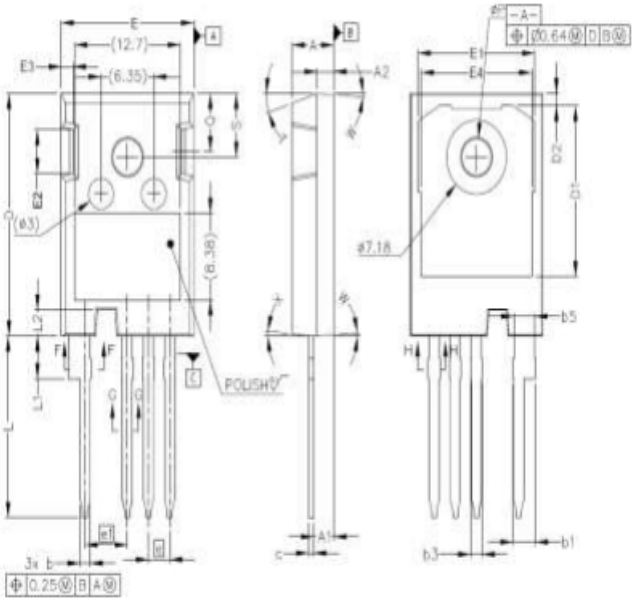
Figure 16. Safe Operating Area

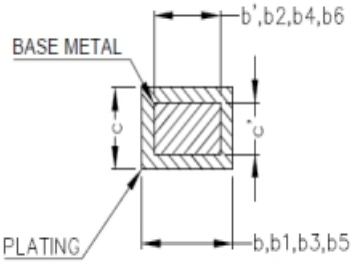
Switching Times Definition and Test Circuit





Package Outline:TO-247-4





SECTION "F-F", "G-G" AND "H-H"
SCALE: NONE

SYMBOL	MILLIMETERS	
	MIN	MAX
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b'	1.07	1.28
b	1.07	1.33
b1	2.39	2.94
b2	2.39	2.84
b3	1.07	1.60
b4	1.07	1.50
b5	2.39	2.69
b6	2.39	2.64
c'	0.55	0.65
c	0.55	0.68
D	23.30	23.60
D1	16.25	17.65
D2	0.95	1.25
E	15.75	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e	2.54 BSC	
e1	5.08 BSC	
N	4	
L	17.31	17.82
L1	3.97	4.37
L2	2.35	2.65
øP	3.51	3.65
Q	5.49	6.00
S	6.04	6.30
T	17.5° REF.	
W	3.5 ° REF.	
X	4° REF.	